

## **TRIAC series**

## **1** Description

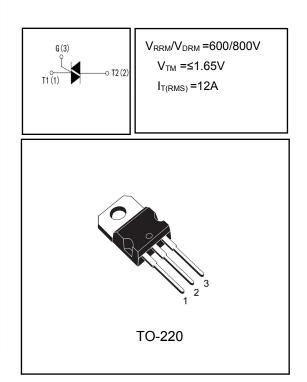
BT138 series triacs with low holding and latchingcurrent are especially recommended for use onmiddle and small resistance type power load.

### 2 Features

- High current output up to 12A
- Low Peak on-state voltage drop
- High voltage
- High reliability

#### **3** Applications

- jet pumps of dishwashers
- fans of air-conditioner
- power charger
- AC Motor control



## **4** Electrical Characteristics

#### **4.1 Absolute Maximum Ratings** (Tc=25°C, unless otherwise noted)

| PARAMETER   |                     | SYMBOL             | VALUE   | UNIT |
|---|---------------------|--------------------|---------|------|
| Repetitive peak off-state voltage (Tj=25°C)                                     | VDRM                | 600/800            | V       |      |
| Repetitive peak reverse voltage (Tj=25°C)                                       |                     | V <sub>RRM</sub>   | 600/800 | V    |
| Non repetitive surge peak Off-state voltage                                     | VDSM                | + 100              | V       |      |
| Non repetitive peak reverse voltage   | V <sub>RSM</sub>    | + 100              | V       |      |
| RMS on-state current  | I <sub>T(RMS)</sub> | 12                 | A       |      |
|   | tp=8.3ms            |                    | 120     |      |
| Non repetitive surge peak on-state current                                      | tp=10ms             | - I <sub>TSM</sub> | 110     | A    |
| I <sup>2</sup> t value for fusing (tp=10ms)                                     | l <sup>2</sup> t    | 72                 | A       |      |
| Repetitive rate of rise of on-state current<br>(ITM=20A IG=50mA dIG/dt 50mA/ms) |                     | dıt/dt             | 50      | A/us |
| Peak gate current   | I <sub>GM</sub>     | 4                  | A       |      |
| Peak gate power   | Р <sub>GM</sub>     | 5                  | W       |      |
| Average gate power dissipation  | P <sub>G(AV)</sub>  | 0.5                | W       |      |
| Operating junction temperature range  | TJ                  | - 40 ~ 125         | °C      |      |
| Storage junction temperature range  | T <sub>STG</sub>    | - 40 ~ 150         | °C      |      |

#### **4.2 Thermal Characteristics**

| PARAMETER                                 | SYMBOL            | VALUE | UNIT |
|---|-------------------|-------|------|
| Thermal Resistance, Junction to Case-sink | R <sub>thJC</sub> | 3.0   | °C/W |





| <b>4.3 Electrical Characteristics</b> (1C=25 C, unless otherwise noted) |  |  |                |     |     |      |      |
|---|--|--|----------------|-----|-----|------|------|
| SYMBOL  | PARAMETER                                  | Test Conditions  |                | Min | Тур | Max  | Unit |
|   |  |  | I - II -III    | -   | -   | 10   |      |
| I <sub>GT</sub>   | Triggering gate current                    | $V_D$ =12V R <sub>L</sub> =33 $\Omega$                                       | IV             | -   | -   | 25   | mA   |
| V <sub>GT</sub>   | Triggering gate voltage                    |  | ALL            | -   | -   | 1.5  | V    |
| $V_{GD}$  | Non-triggering gate voltage                | V <sub>D</sub> =V <sub>DRM</sub> T <sub>j</sub> =125°C R <sub>L</sub> =3.3KΩ |                | 0.2 | -   | -    | V    |
|   |  |  | I -III         | -   | -   | 30   |      |
| ١L  | Latching Current                           | I <sub>G</sub> =1.2I <sub>GT</sub>   | II -IV         | -   | -   | 40   | mA   |
| Ι <sub>Η</sub>  | Holding Current                            | I <sub>T</sub> =100mA  |                | -   | -   | 30   | mA   |
| d <sub>V/dt</sub>   | Critical Rate of Rise of Off-state Voltage | V <sub>D</sub> =2/3V <sub>DRM</sub> Gate Open T <sub>j</sub> =125℃           |                | 20  | -   | -    | V/us |
| V <sub>TM</sub>   | Peak Forward On-State Voltage              | I <sub>™</sub> =15A tp=380us   |                | -   | -   | 1.65 | V    |
| I <sub>DRM</sub>  | Maximum forward or reverse leakage current |  | <b>Tj=25</b> ℃ | -   | -   | 10   | uA   |
| I <sub>RRM</sub>  | Maximum reverse leakage current            | VD=VDRM VR=VRRM  | Tj=125℃        | -   | -   | 500  | uA   |

#### **4.3 Electrical Characteristics** (Tc=25°C, unless otherwise noted)

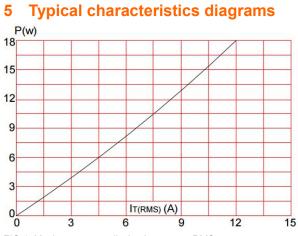


FIG.1: Maximum power dissipation versus RMS on-state current

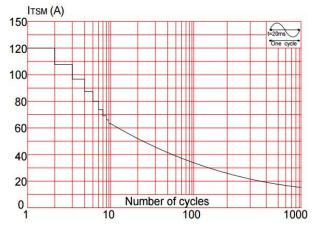
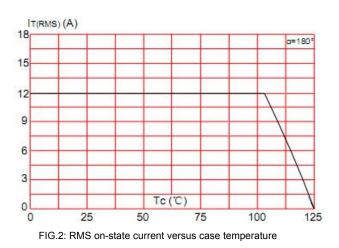
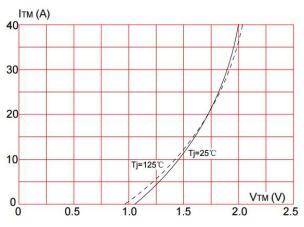


FIG.3: Surge peak on-state current versus number of cycles









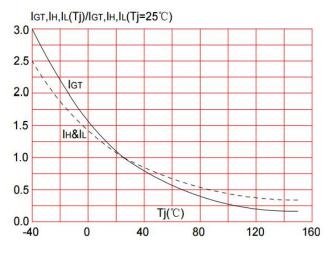
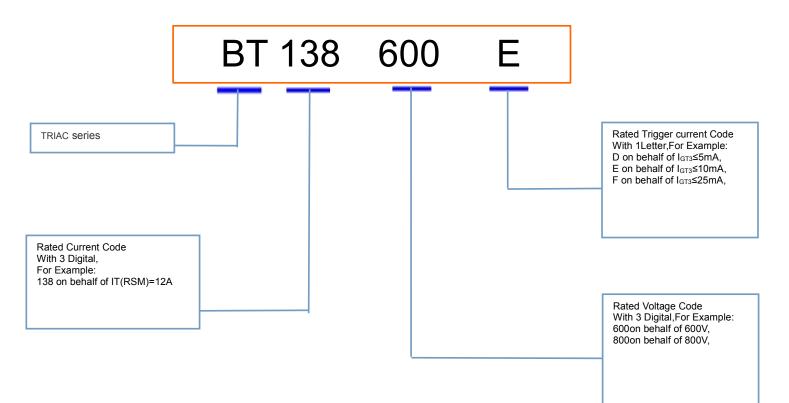


FIG.5: Relative variations of gate trigger current, holding current and latching current versus junction temperature

## 6 Product Names Rules



## 7 Product Specifications and Packaging Models

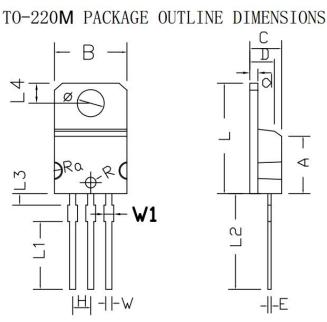
| Product Model | Package Type | Mark Name | RoHS    | Package | Quantity  |
|---------------|--------------|-----------|---------|---------|-----------|
| BT138         | TO-220       | BT138     | Pb-free | Tube    | 1000//box |





## **8 Dimensions**

# В Ø ARa W1 H-1-W



| Cumb a 1 | Dimensions I | n Millimeters | Dimensions | In Inches |
|----------|--------------|---------------|------------|-----------|
| Symbol   | min.         | max.          | min.       | max.      |
|          | MIN          | MAX           | MIN        | MAX       |
| Α        | 8.03         | 8.05          | 0.316      | 0.317     |
| В        | 10.13        | 10.23         | 0.399      | 0.403     |
| С        | 4.42         | 4.52          | 0.174      | 0.178     |
| D        | 3.42         | 3.52          | 0.135      | 0.139     |
| Е        | 0.44         | 0.46          | 0.017      | 0.018     |
| L        | 15.25        | 15.45         | 0.601      | 0.609     |
| Н        | 2.52         | 2.56          | 0.099      | 0.101     |
| W        | 0.85         | 0.87          | 0.033      | 0.034     |
| Φ        | 3.78         | 3.82          | 0.149      | 0.151     |
| R        | 0.74         | 0.76          | 0.029      | 0.030     |
| Ra       | 9.44         | 9.48          | 0.372      | 0.374     |
| d        | 1.28         | 1.32          | 0.050      | 0.052     |
| L1       | 9.4          | 9.6           | 0.370      | 0.378     |
| L2       | 13.22        | 13.62         | 0. 521     | 0.537     |
| L3       | 1.52         | 1.72          | 0.060      | 0.068     |
| L4       | 2.7          | 2.9           | 0.106      | 0.114     |
| W1       | 1.32         | 1.42          | 0.052      | 0.056     |

#### **Attentions** 9

- Jiangsu Donghai Semiconductor Technology Co., Ltd. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of WXDH products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

## 10 Appendix

Revision history:

| Date      | REV. | Description | Page |
|-----------|------|-------------|------|
| 2017.09.8 | 1.0  | Original    |      |